STF8N80K5, STFI8N80K5

N-channel 800 V, 0.8 Ω typ., 6 A MDmesh™ K5 Power MOSFET in TO-220FP and I^2PAKFP packages

Datasheet – production data

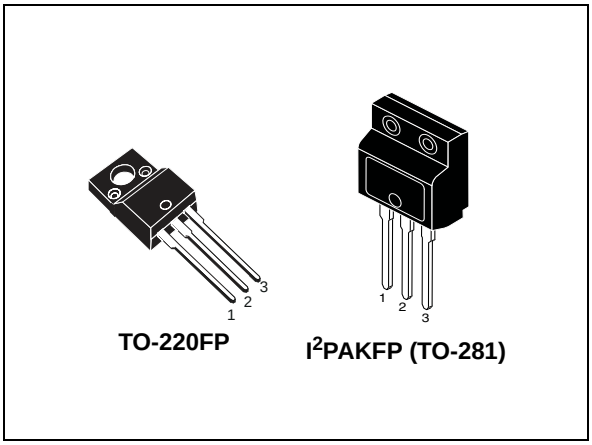
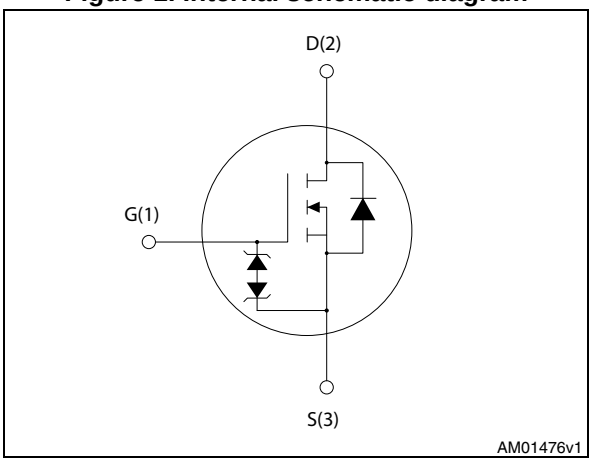


Figure 1. Internal schematic diagram



Features

Order codes	V_{DS}	$R_{DS(on)}$max.	I_D	P_{TOT}
STF8N80K5	800 V	0.95 Ω	6 A	25 W
STFI8N80K5				

- Industry's lowest $R_{DS(on)}$ x area
- Industry's best figure of merit (FoM)
- Ultra low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These very high voltage N-channel Power MOSFETs are designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STF8N80K5	8N80K5	TO-220FP	Tube
STFI8N80K5		I^2PAKFP (TO-281)	

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current T_C = 25 °C	6 (1)	A
I_D	Drain current T_C = 100 °C	4 (1)	A
I_{DM} (2)	Drain current (pulsed)	24 (1)	A
P_{TOT}	Total dissipation at T_C = 25 °C	25	W
I_{AR} (3)	Max current during repetitive or single pulse avalanche	2	A
E_{AS} (4)	Single pulse avalanche energy (starting T_J = 25 °C, I_D=I_{AS}, V_{DD}= 50 V)	114	mJ
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s;T_C=25 °C)	2500	V
dv/dt (5)	Peak diode recovery voltage slope	4.5	V/ns
dv/dt (6)	MOSFET dv/dt ruggedness	50	V/ns
T_j	Operating junction temperature	-55 to 150	°C
T_{stg}	Storage temperature		°C

1. Limited by package.
2. Pulse width limited by safe operating area.
3. Pulse width limited by $T_{Jmax.}$
4. Starting T_J = 25 °C, I_D=I_{AS}, V_{DD}= 50 V
5. $I_{SD} \leq$ 6 A, di/dt $\leq$ 100 A/µs, $V_{DS(peak)} \leq V_{(BR)DSS}$
6. $V_{DS} \leq$ 640 V

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max.	5	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-amb max.	62.5	°C/W

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS}= 0	800			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 800 V,			1	µA
		V_{DS} = 800 V, Tc=125 °C			50	µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ± 20 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D= 3 A		0.8	0.95	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} =100 V, f=1 MHz, V_{GS}=0	-	450	-	pF
C_{oss}	Output capacitance		-	50	-	pF
C_{rss}	Reverse transfer capacitance		-	1	-	pF
$C_{o(tr)}$(1)	Equivalent capacitance time related	V_{GS} = 0, V_{DS} = 0 to 640 V	-	57	-	pF
$C_{o(er)}$(2)	Equivalent capacitance energy related		-	24	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz open drain	-	6	-	Ω
Q_g	Total gate charge	V_{DD} = 640 V, I_D = 6 A V_{GS} =10 V *(see Figure 16)*	-	16.5	-	nC
Q_{gs}	Gate-source charge		-	3.2	-	nC
Q_{gd}	Gate-drain charge		-	11	-	nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 400 V, I_D = 3 A, R_G=4.7 Ω, V_{GS}=10 V *(see Figure 18)*	-	12	-	ns
t_r	Rise time			14	-	ns
$t_{d(off)}$	Turn-off delay time			32	-	ns
t_f	Fall time			20	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		6	A
I_{SDM}	Source-drain current (pulsed)				24	A
V_{SD} (1)	Forward on voltage	I_{SD}= 6 A, V_{GS}=0	-		1.5	V
t_{rr}	Reverse recovery time	I_{SD}= 6 A, V_{DD}= 60 V di/dt = 100 A/µs, *(see Figure 17)*	-	300		ns
Q_{rr}	Reverse recovery charge			3		µC
I_{RRM}	Reverse recovery current			20		A
t_{rr}	Reverse recovery time	I_{SD}= 6 A, V_{DD}= 60 V di/dt=100 A/µs, Tj=150 °C *(see Figure 17)*	-	415		ns
Q_{rr}	Reverse recovery charge		-	3.8		µC
I_{RRM}	Reverse recovery current		-	18		A

1. Pulsed: pulse duration = 300µs, duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	I_{GS} = ± 1mA, I_D=0	30	-	-	V

The built-in back-to-back Zener diodes have been specifically designed to enhance the ESD capability of the device. The Zener voltage is appropriate for efficient and cost-effective intervention to protect the device integrity. These integrated Zener diodes thus eliminate the need for external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

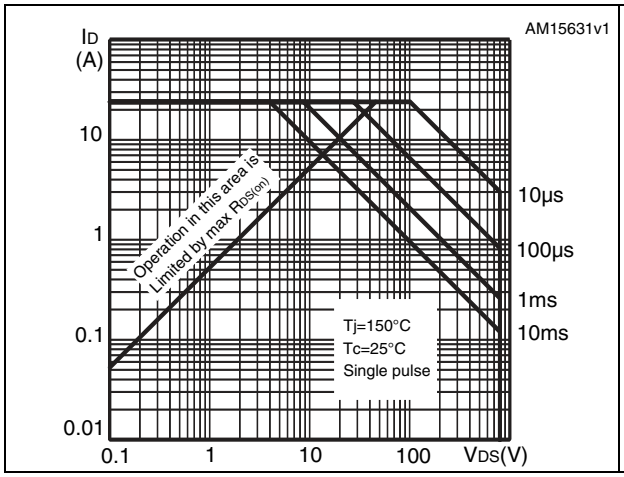


Figure 3. Thermal impedance

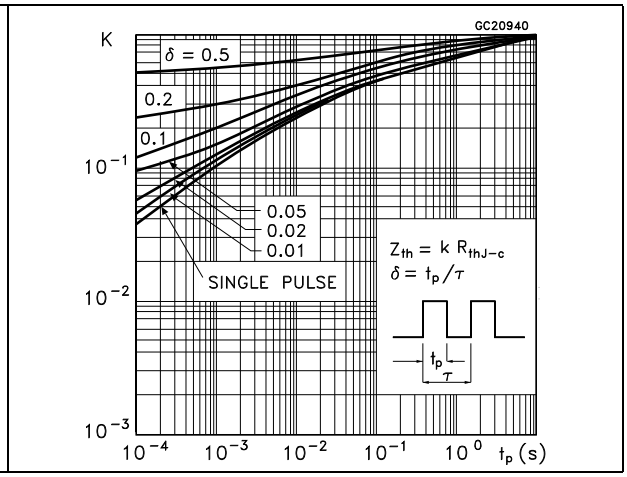


Figure 4. Output characteristics

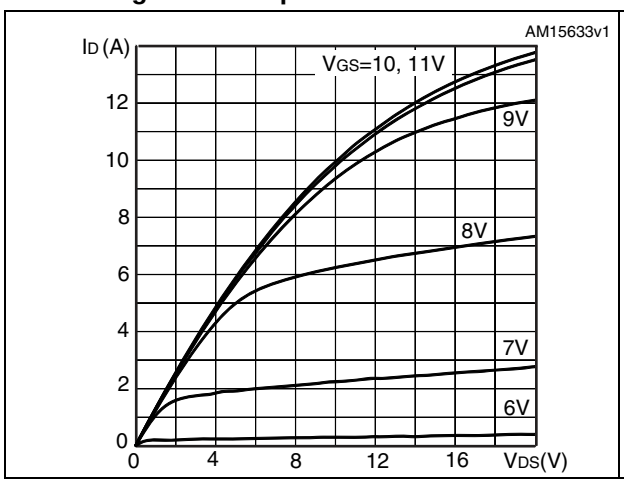


Figure 5. Transfer characteristics

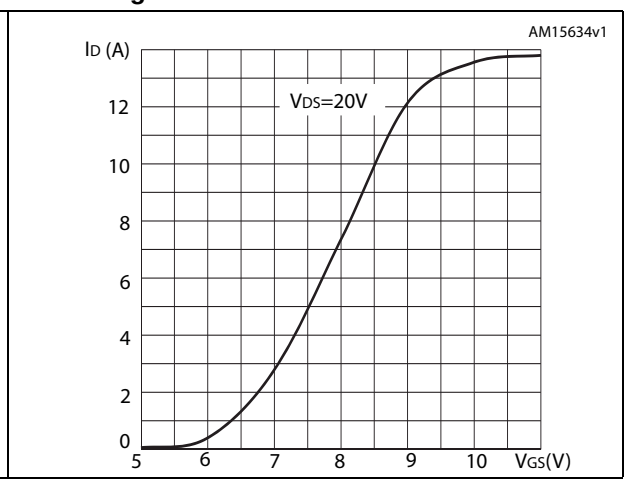


Figure 6. Gate charge vs gate-source voltage

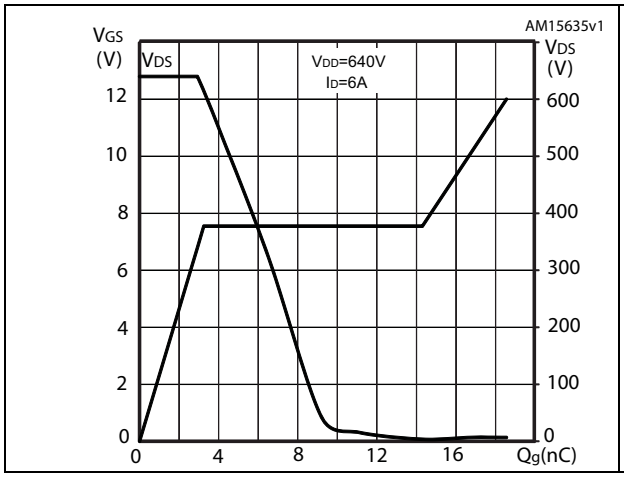


Figure 7. Static drain-source on-resistance

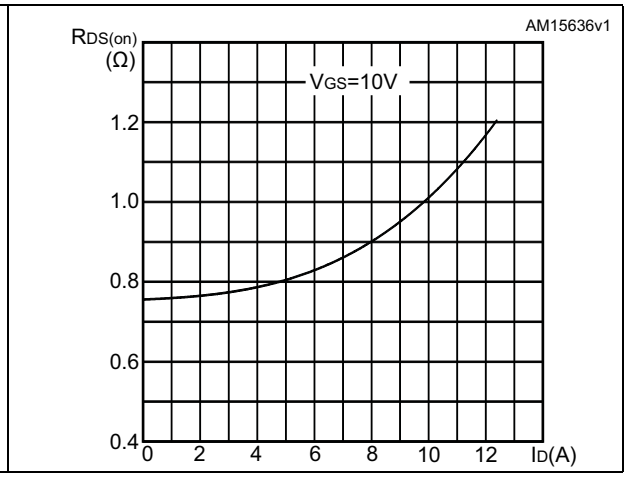


Figure 8. Capacitance variations

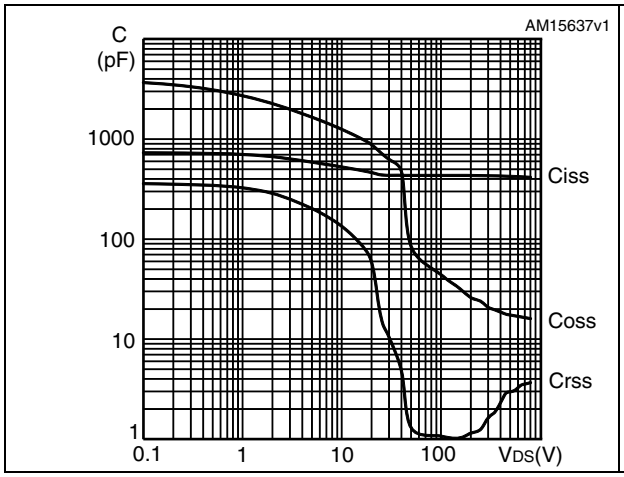


Figure 9. Output capacitance stored energy

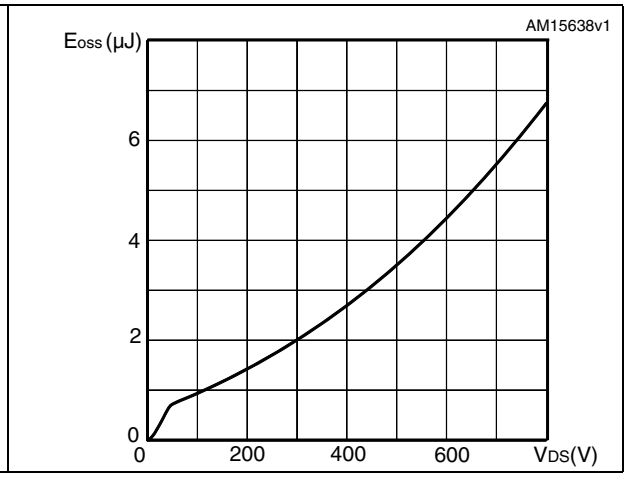


Figure 10. Normalized gate threshold voltage vs. temperature

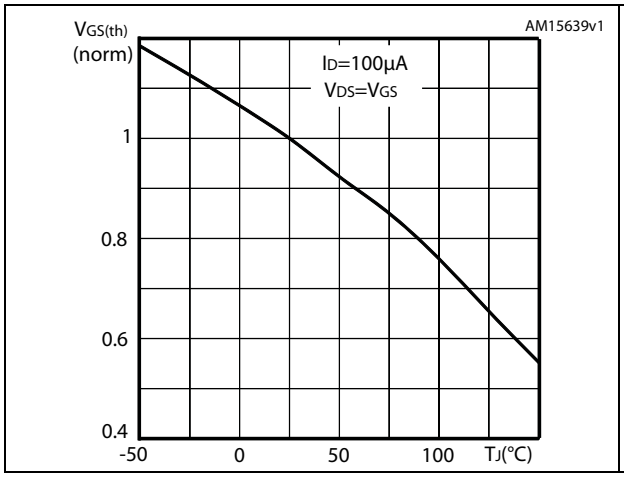


Figure 11. Normalized on-resistance vs. temperature

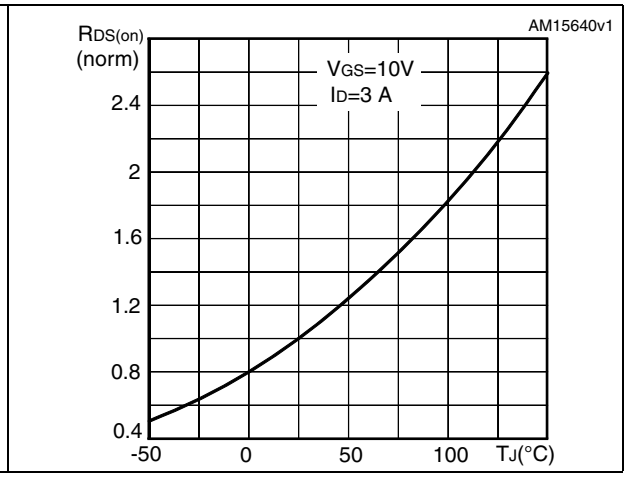


Figure 12. Drain-source diode forward characteristics

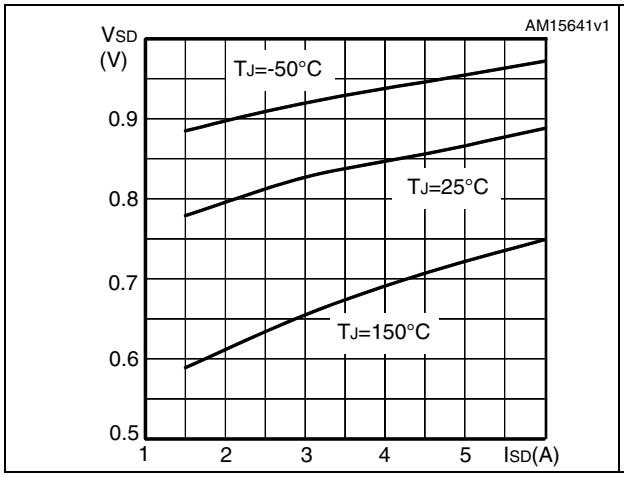


Figure 13. Normalized V_{DS} vs. temperature

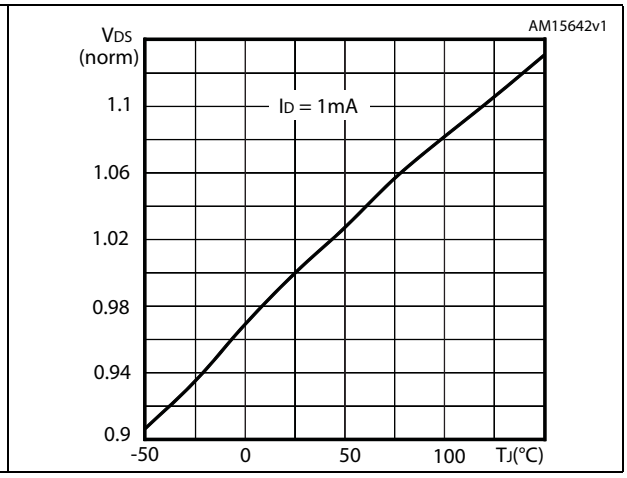
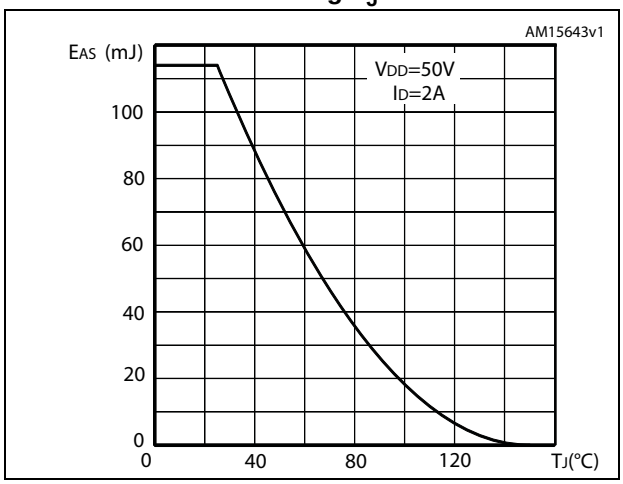


Figure 14. Maximum avalanche energy vs. starting T_J



3 Test circuits

Figure 15. Switching times test circuit for resistive load

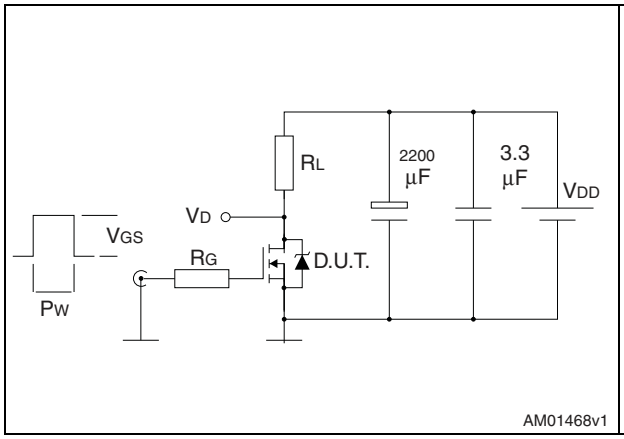


Figure 16. Gate charge test circuit

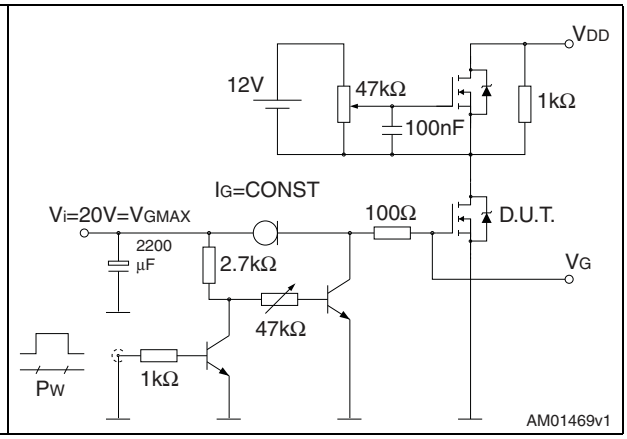


Figure 17. Test circuit for inductive load switching and diode recovery times

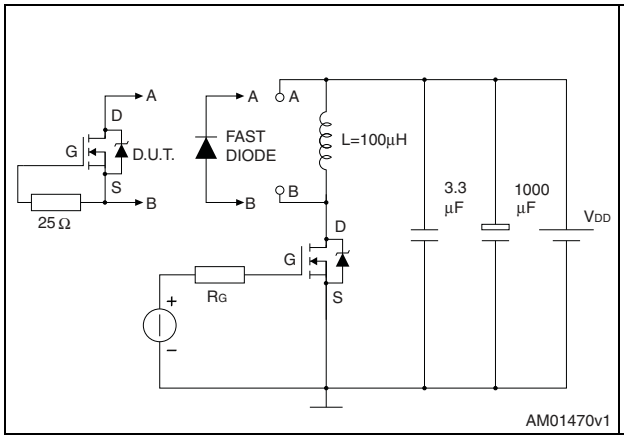


Figure 18. Unclamped inductive load test circuit

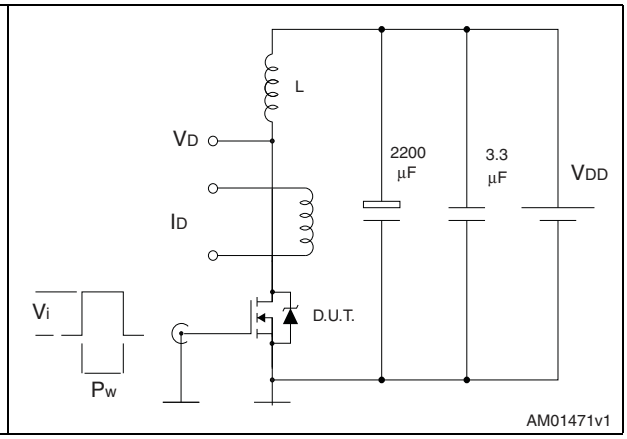


Figure 19. Unclamped inductive waveform

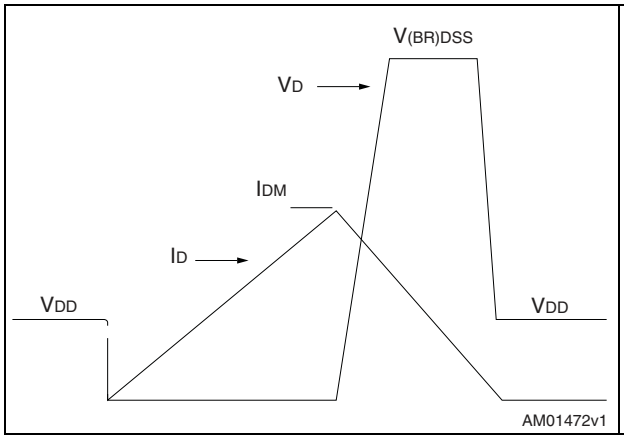
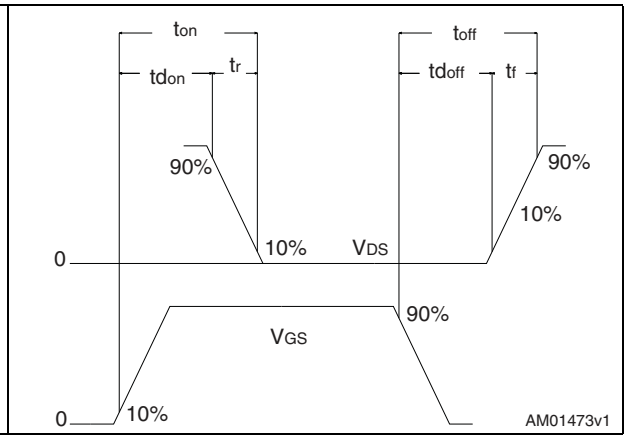


Figure 20. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

Figure 21. TO-220FP drawing

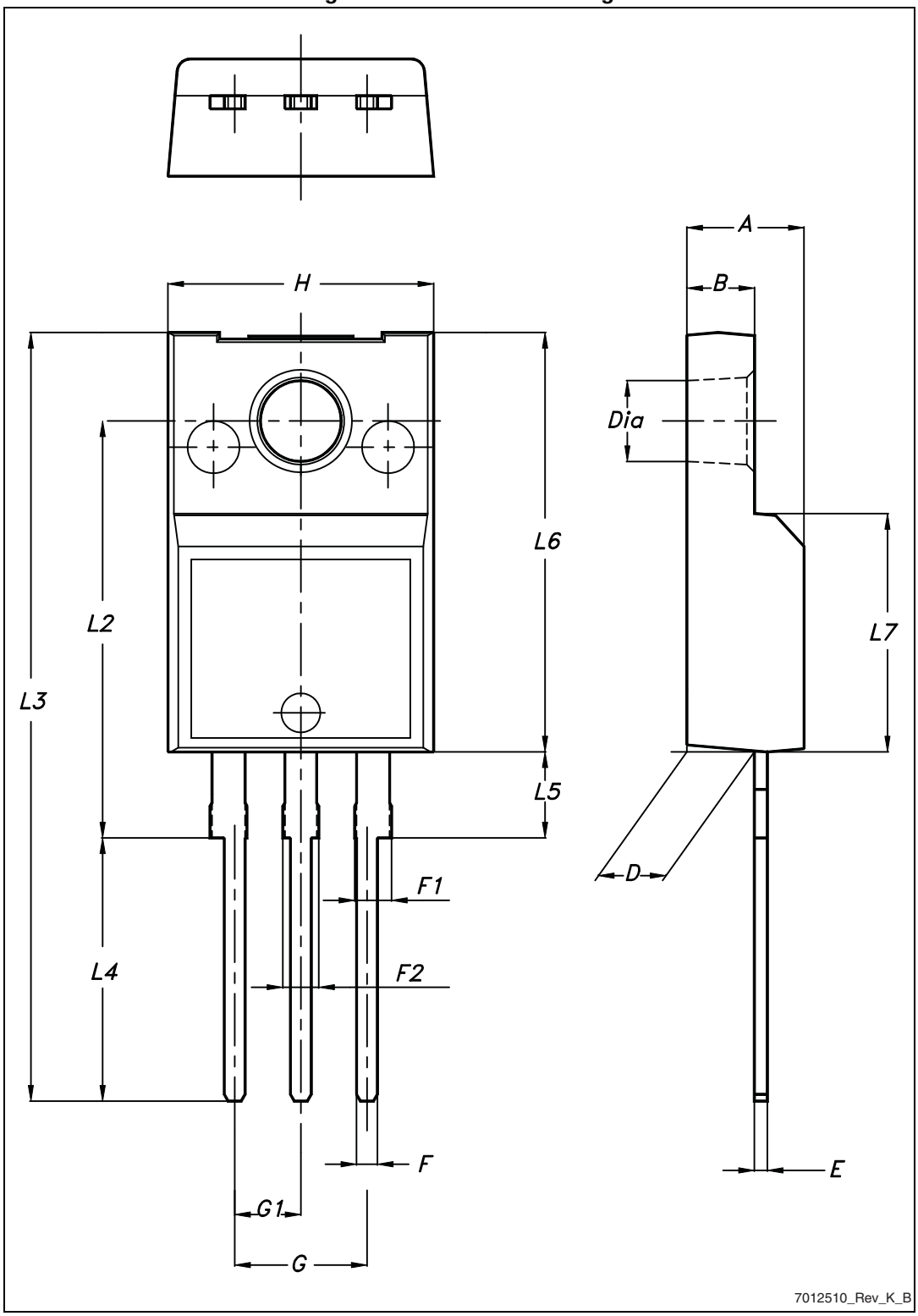


Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 22. I²PAKFP (TO-281) drawing

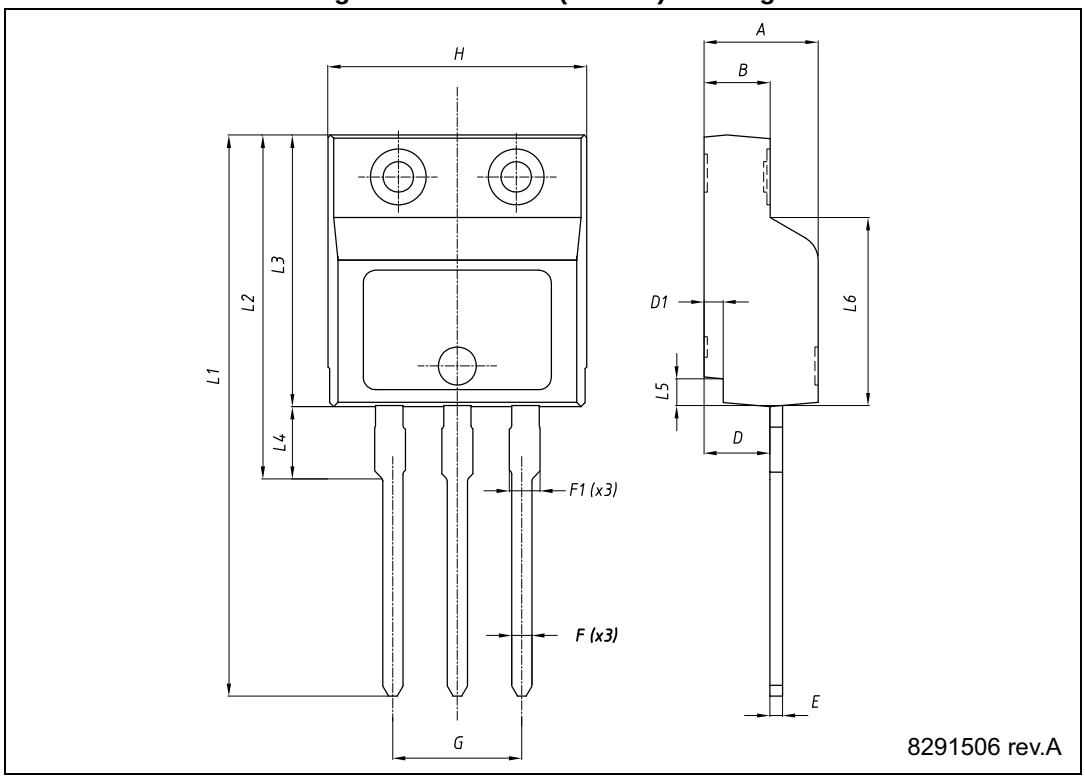


Table 10. I²PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95	-	5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.30		7.50

5 Revision history

Table 11. Document revision history

Date	Revision	Changes
25-Mar-2012	1	First release. Part numbers previously included in datasheet DM00062075
27-Mar-2013	2	Added: MOSFET dv/dt ruggedness on *Table 2*
28-Oct-2014	3	Updated title with “MDmesh™ K5” nomenclature Document status promoted from preliminary data to production data Updated cover page *Features* list Updated cover page *Description* Updated zener diode descriptions in *Section 2: Electrical characteristics* Updated *Figure 7: Static drain-source on-resistance* Reordered drawings and tables in *Section 4: Package mechanical data*